

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S10 2	16	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light ADJ3 emit\$4 ADJ3 device) or (light-emit\$4 ADJ3 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near2 (layer or medium or region or film))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/03 11:46
S10 7	0	(kenneth near3 vilhelmsson).in.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/03 11:55
S92	65	ekawa.in.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/03 11:55
S11 0	0	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light ADJ3 emit\$4 ADJ3 device) or (light-emit\$4 ADJ3 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near2 (layer or medium or region or film))).clm.	US-PGPUB	AND	ON	2006/03/03 11:56
S10 9	0	(kenneth near3 vilhelmsson).in. and "372"/\$.ccls.	US-PGPUB	AND	ON	2006/03/03 11:56
S10 8	1	(kenneth near3 vilhelmsson).in.	US-PGPUB	AND	ON	2006/03/03 11:56
S10 6	1	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light ADJ3 emit\$4 ADJ3 device) or (light-emit\$4 ADJ3 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near2 (layer or medium or region or film))	USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/03 11:56
S10 5	32	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light ADJ3 emit\$4 ADJ3 device) or (light-emit\$4 ADJ3 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near2 (layer or medium or region or film))	US-PGPUB; USPAT	AND	ON	2006/04/12 09:23
S11 3	0	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light ADJ3 emit\$4 ADJ3 device) or (light-emit\$4 ADJ3 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and ((guide near2 (layer or medium or region or film)) with (Al with Ga with As))	US-PGPUB; USPAT	AND	ON	2006/04/12 09:27
S11 2	15	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light ADJ3 emit\$4 ADJ3 device) or (light-emit\$4 ADJ3 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and ((guide near2 (layer or medium or region or film)) with (AlGaAs))	US-PGPUB; USPAT	AND	ON	2006/04/12 09:27
S11 1	0	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light ADJ3 emit\$4 ADJ3 device) or (light-emit\$4 ADJ3 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and ((guide near2 (layer or medium or region or film)) with (Al with Ga with Ga))	US-PGPUB; USPAT	AND	ON	2006/04/12 09:27